

TECHNICAL DATA DATA SHEET D0112 REV. –

SILICON SCHOTTKY RECTIFIER DIE

Applications:

• Switching Power Supply • Converters • Free-Wheeling Diodes • Polarity Protection Diode

Features:

- Ultra low Reverse Leakage Current
- Soft Reverse Recovery at Low and High Temperature
- Very Low Forward Voltage Drop
- Low Power Loss, High Efficiency
- High Surge Capacity
- Guard Ring for Enhanced Durability and Long Term Reliability
- Guaranteed Reverse Avalanche Characteristics
- Electrically / Mechanically Stable during and after Packaging

Maximum Ratings:

Characteristics	Symbol	Condition	Max.	Units
Peak Inverse Voltage	V _{RWM}	-	45	V
Average Forward Current	I _{F(AV)}	50% duty cycle, rectangular wave form	15	A
Peak One Cycle Non- Repetitive Surge Current	I _{FSM}	8.3 ms, Sine pulse ⁽¹⁾	280	A
Junction Temperature	TJ	-	-55 to +175	°C
Storage Temperature	T _{stg}	-	-55 to +175	°C

Electrical Characteristics:

Characteristics	Symbol	Condition	Max.	Units
Forward Voltage Drop	V _{F1}	@ 15A, Pulse, T _J = 25 °C	0.64	V
	V _{F2}	@ 15A, Pulse, T _J = 125 °C	0.57	>
Reverse Current	I _{R1}	$@V_R = 45V$, Pulse,	0.4	mA
		T _J = 25 °C		
	I _{R2}	$@V_R = 45V$, Pulse,	15	mA
		T _J = 125 °C		
Junction Capacitance	Ст	@V _R = 5V, T _C = 25 °C	800	pF
		f _{SIG} = 1MHz,		
		V _{SIG} = 50mV (p-p)		

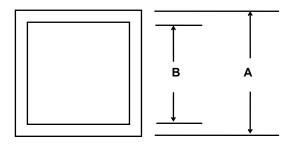
(1) in SHD package

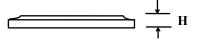




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Mechanical Dimensions: In Inches (mm)





Bottom side metalization Ag-5kA minimum Top side metalization Ag-25kA minimum Bottom side is cathode, top side is anode Dimension H =0.0105±0.001(0.27±0.026) (It can be customized according to customer requirements)

Α	В
0.125 ± 0.003(3.18 ± 0.08)	0.116 ± 0.003(2.95 ± 0.08)

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